AUTOMOTIVE

COMPLIANT HALOGEN

FREE



# Vishay Semiconductors

## Silicon PIN Photodiode



#### **DESCRIPTION**

TEMD7100X01 is a high speed and high sensitive PIN photodiode. It is a miniature surface mount device (SMD) including the chip with a 0.23 mm<sup>2</sup> sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength of 830 nm to 950 nm.

#### **FEATURES**

• Package type: surface mount

• Package form: 0805

• Dimensions (L x W x H in mm): 2 x 1.25 x 0.85

• Radiant sensitive area (in mm<sup>2</sup>): 0.23

· High radiant sensitivity

 Daylight blocking filter matched with 830 nm to 950 nm emitters

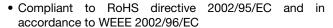


• Angle of half sensitivity:  $\varphi = \pm 60^{\circ}$ 

• Floor life: 168 h, MSL 3, acc. J-STD-020

· Lead (Pb)-free reflow soldering

• AEC-Q101 qualified



• Halogen-free according to IEC 61249-2-21 definition

#### **APPLICATIONS**

- High speed photo detector
- · Infrared remote control
- Infrared data transmission
- Photo interrupters
- Shaft encoders

PRODUCT SUMMARY			
COMPONENT	I <sub>ra</sub> (μΑ)	φ (deg)	λ <sub>0.5</sub> (nm)
TEMD7100X01	3	± 60	750 to 1050

#### Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE PACKAGING		REMARKS	PACKAGE FORM	
TEMD7100X01	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	0805	

#### Note

• MOQ: minimum order quantity

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_{R}$	60	V
Power dissipation	T <sub>amb</sub> ≤ 25 °C	P <sub>V</sub>	215	mW
Junction temperature		Tj	100	°C
Operating temperature range		T <sub>amb</sub>	- 40 to + 100	°C
Storage temperature range		T <sub>stg</sub>	- 40 to + 100	°C
Soldering temperature	Acc. reflow solder profile fig. 8	T <sub>sd</sub>	260	°C
Thermal resistance junction/ambient	Acc. J-STD-051	R <sub>thJA</sub>	270	K/W

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PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I <sub>F</sub> = 50 mA	V <sub>F</sub>		1		V
Breakdown voltage	I <sub>R</sub> = 100 μA, E = 0	V <sub>(BR)</sub>	60			V
Reverse dark current	V <sub>R</sub> = 10 V, E = 0	I <sub>ro</sub>		1	3	nA
Diode capacitance	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	C <sub>D</sub>		4		pF
	V <sub>R</sub> = 5 V, f = 1 MHz, E = 0	C <sub>D</sub>		1.3		pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of Vo	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK <sub>Vo</sub>		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	l <sub>k</sub>		3		μΑ
Temperature coefficient of I <sub>k</sub>	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK <sub>lk</sub>		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \ \lambda = 950 \text{ nm}, \\ V_R = 5 \text{ V}$	I <sub>ra</sub>	2.4	3	3.6	μΑ
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		$\lambda_{p}$		950		nm
Range of spectral bandwidth		λ <sub>0.5</sub>		750 to 1050		nm
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t <sub>r</sub>		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t <sub>f</sub>		100		ns

## **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

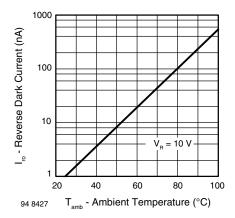


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

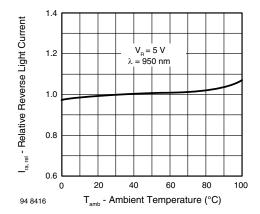


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



## Silicon PIN Photodiode

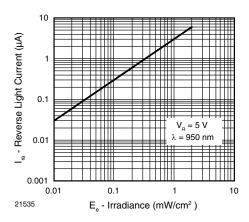


Fig. 3 - Reverse Light Current vs. Irradiance

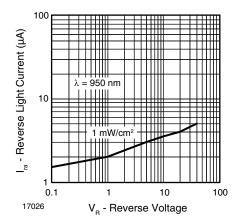


Fig. 4 - Reverse Light Current vs. Reverse Voltage

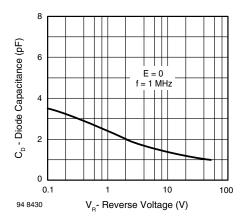


Fig. 5 - Diode Capacitance vs. Reverse Voltage

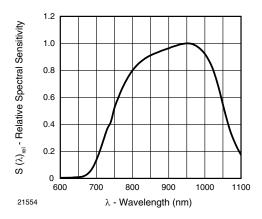


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

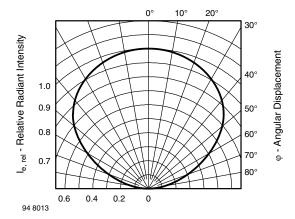


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

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### **REFLOW SOLDER PROFILE**

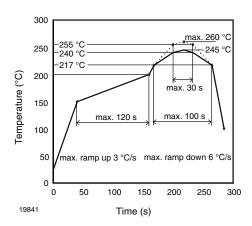


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

#### **DRYPACK**

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

#### **FLOOR LIFE**

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 168 h

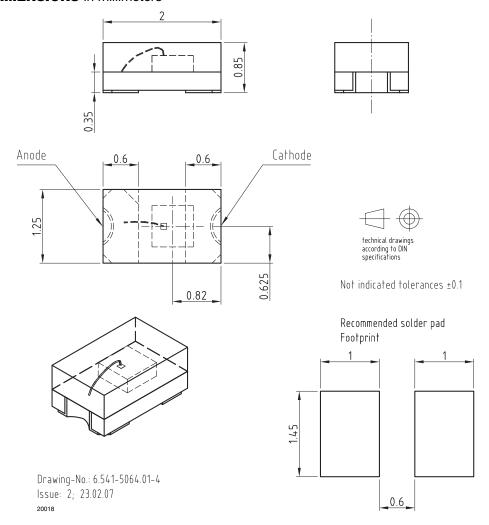
Conditions:  $T_{amb}$  < 30 °C, RH < 60 %

Moisture sensitivity level 3, acc. to J-STD-020.

#### **DRYING**

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40  $^{\circ}$ C (+ 5  $^{\circ}$ C), RH < 5 %.

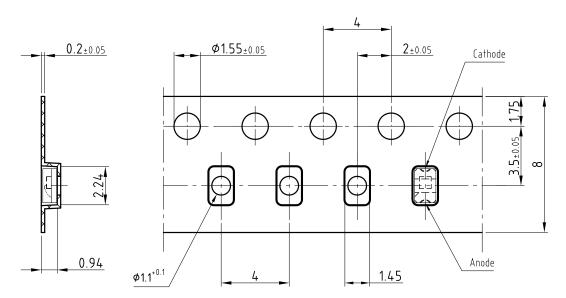
#### **PACKAGE DIMENSIONS** in millimeters



## Silicon PIN Photodiode

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### **BLISTER TAPE DIMENSIONS** in millimeters



Reel off direction

technical drawings according to DIN specifications

Drawing-No.: 9.700-5311.01-4

Issue: 1; 23.02.07

21501

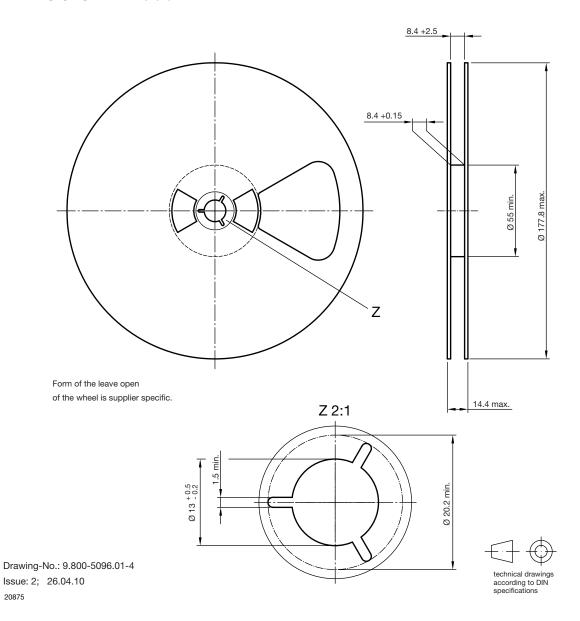
Not indicated tolerances ±0.1

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## **REEL DIMENSIONS** in millimeters



20875





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